

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD1762

DESCRIPTION

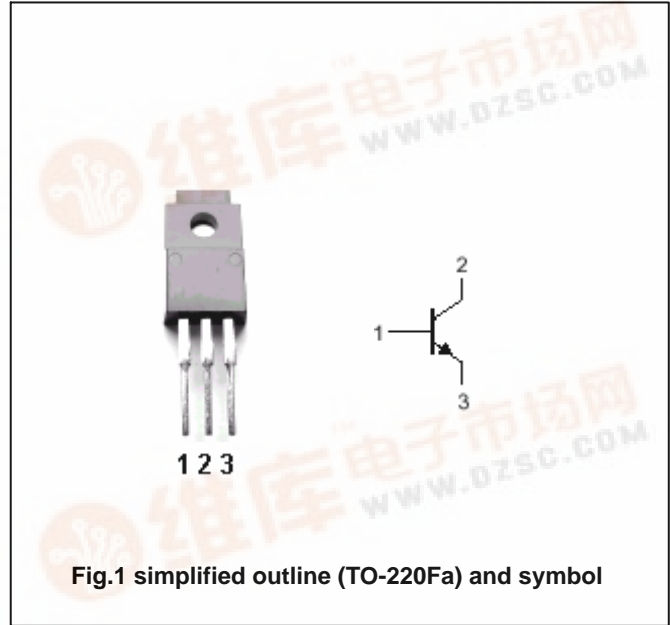
- With TO-220Fa package
- Low collector saturation voltage
- Complement to type 2SB1185

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	50	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		3	A
I _{CM}	Collector current-Peak		4.5	A
P _C	Collector power dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA, I _B =0	50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =50 μA, I _E =0	60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50 μA, I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.2A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =40V, I _E =0			1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			1	μA
h _{FE}	DC current gain	I _C =0.5A; V _{CE} =3V	60		320	
f _T	Transition frequency	I _E =-0.5A; V _{CE} =5V; f=30MHz		90		MHz
C _{ob}	Output capacitance	I _E =0; V _{CB} =10V, f=1MHz		40		pF

◆ h_{FE} Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

